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April 1st, 2010 Renesas Electronics Corporation

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R1LV0414D Series

4M SRAM (256-kword \times 16-bit)

REJ03C0312-0100 Rev.1.00 May.24.2007

Description

The R1LV0414D is a 4-Mbit static RAM organized 256-kword \times 16-bit, fabricated by Renesas's high-performance 0.15 μ m CMOS and TFT technologies. R1LV0414DSeries has realized higher density, higher performance and low power consumption. The R1LV0414D Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has packaged in 44-pin TSOP II.

Features

Single 3.0 V supply: 2.7 V to 3.6 V
Fast access time: 55/70 ns (max)

• Power dissipation:

— Standby: $3 \mu W \text{ (typ) } (V_{CC} = 3.0 \text{ V})$

• Equal access and cycle times

• Common data input and output.

— Three state output

• Battery backup operation.

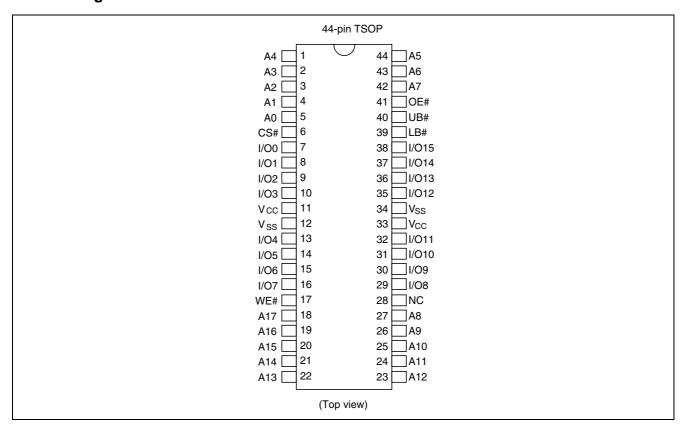
• Temperature range: -40 to +85°C

Ordering Information

Type No.	Access time	Package
R1LV0414DSB-5SI	55 ns	400-mil 44-pin plastic TSOP II (44P3W-H)
R1LV0414DSB-7LI	70 ns	



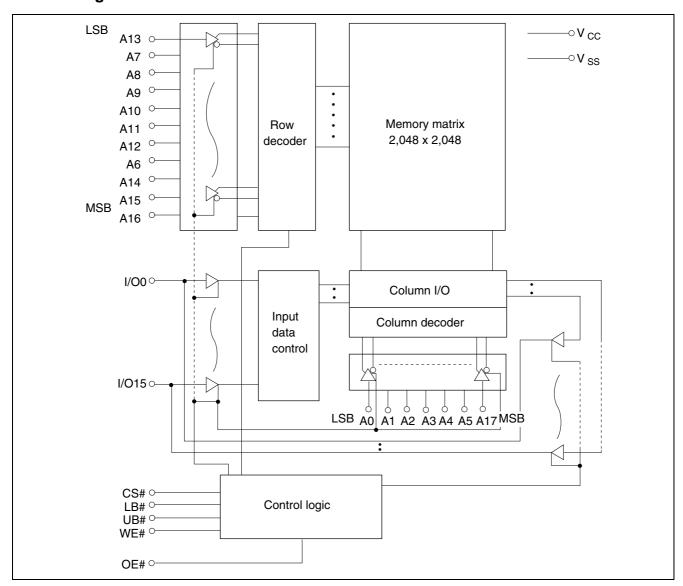
Pin Arrangement



Pin Description

Pin name	Function
A0 to A17	Address input
I/O0 to I/O15	Data input/output
CS# (CS)	Chip select
OE# (OE)	Output enable
WE# (WE)	Write enable
LB# (LB)	Lower byte select
UB# (UB)	Upper byte select
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

Block Diagram



Operation Table

CS#	WE#	OE#	UB#	LB#	I/O0 to I/O7	I/O8 to I/O15	Operation
Н	×	×	×	×	High-Z	High-Z	Standby
×	×	×	Н	Н	High-Z	High-Z	Standby
L	Н	L	L	L	Dout	Dout	Read
L	Н	L	Н	L	Dout	High-Z	Lower byte read
L	Н	L	L	Н	High-Z	Dout	Upper byte read
L	L	×	L	L	Din	Din	Write
L	L	×	Н	L	Din	High-Z	Lower byte write
L	L	×	L	Н	High-Z	Din	Upper byte write
L	Н	Н	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V _{SS}	V _{CC}	−0.5 to +4.6	V
Terminal voltage on any pin relative to V _{SS}	V _T	-0.5^{*1} to $V_{CC} + 0.3^{*2}$	V
Power dissipation	P _T	0.7	W
Operating temperature	Topr	-40 to +85	°C
Storage temperature range	Tstg	−65 to +150	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Notes: 1. V_T min: -3.0 V for pulse half-width ≤ 30 ns.

2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit	Note
Supply voltage	V _{CC}	2.7	3.0	3.6	V	
	V _{SS}	0	0	0	V	
Input high voltage	V _{IH}	2.2	_	$V_{CC} + 0.3$	V	
Input low voltage	V_{IL}	-0.3	_	0.6	V	1
Ambient temperature range	Та	-40	_	+85	°C	

Note: 1. V_{IL} min: -3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

Pai	ameter		Symbol	Min	Тур	Max	Unit	Test conditions
Input leakage curre	ent		I _{LI}	_	_	1	μΑ	Vin = V _{SS} to V _{CC}
Output leakage current			I _{LO}	_	_	1	μΑ	$CS\# = V_{IH}$ or $OE\# = V_{IH}$ or $WE\# = V_{II}$ or $LB\# = UB\# = V_{IH}$,
								$V_{I/O} = V_{SS}$ to V_{CC}
Operating current			I _{cc}	_	_	20	mA	$CS\# = V_{IL}$, Others = V_{IH}/V_{IL} , $I_{I/O} = 0$ mA
Average operating current			I _{CC1}	_	—	25	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, CS# = V_{IL} , Others = V_{IH}/V_{IL}
			I _{CC2}	_		5	mA	Cycle time = 1 μ s, duty = 100%, $I_{I/O}$ = 0 mA, CS# \leq 0.2 V, $V_{IH} \geq V_{CC} - 0.2$ V, $V_{IL} \leq$ 0.2 V
Standby current			I _{SB}	_	0.1*1	0.3	mA	CS# = V _{IH}
Standby current	-5SI	to +85°C	I _{SB1}	_	_	10		Vin ≥ 0 V
-		to +70°C	I _{SB1}	_	_	8	μA	(1) CS# ≥ V _{CC} – 0.2 V
		to +40°C	I _{SB1}	_	_	3	μΑ	(2) LB# = UB# \geq V _{CC} $-$ 0.2 V,
		to +25°C	I _{SB1}	_	1* ¹	2.5	μΑ	CS# ≤ 0.2 V
	-7LI	to +85°C	I _{SB1}	_	_	20	μΑ	Average values
		to +70°C	I _{SB1}			16	μΑ	
	to +40°C		I _{SB1}	_		10	μΑ	
to +25°C			I _{SB1}	_	1* ¹	10	μΑ	
Output high voltage			V_{OH}	2.4		_	V	$I_{OH} = -1 \text{ mA}$
			V_{OH2}	$V_{CC}-0.2$	_	_	V	$I_{OH} = -100 \mu A$
Output low voltage			V_{OL}	_	_	0.4	V	I _{OL} = 2 mA
			V_{OL2}	_	_	0.2	V	I _{OL} = 100 μA

Notes: 1. Typical values are at $V_{CC} = 3.0 \text{ V}$, $Ta = +25^{\circ}\text{C}$ and specified loading, and not guaranteed.

Capacitance

 $(Ta = +25^{\circ}C, f = 1.0 \text{ MHz})$

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	Note
Input capacitance	Cin	_	_	8	pF	Vin = 0 V	1
Input/output capacitance	C _{I/O}	_	_	10	pF	$V_{I/O} = 0 V$	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, V_{CC} = 2.7 \text{ V to } 3.6 \text{ V})$

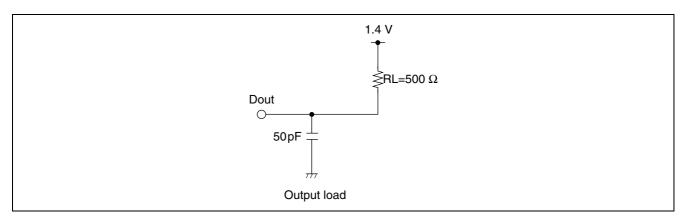
Test Conditions

• Input pulse levels: $V_{IL} = 0.4 \text{ V}$, $V_{IH} = 2.4 \text{ V}$

• Input rise and fall time: 5 ns

Input/output timing reference levels: 1.4 V

• Output load: See figures (Including scope and jig)



Read Cycle

			R1LV				
		-5	SI	-7	'LI	1	
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	55	_	70	_	ns	
Address access time	t _{AA}	_	55	_	70	ns	
Chip select access time	t _{ACS}	_	55	_	70	ns	
Output enable to output valid	t _{OE}	_	35	_	40	ns	
Output hold from address change	t _{OH}	10	_	10	_	ns	
LB#, UB# access time	t _{BA}	_	55	_	70	ns	
Chip select to output in low-Z	t _{CLZ}	10	_	10	_	ns	2, 3
LB#, UB# disable to low-Z	t _{BLZ}	5	—	5	—	ns	2, 3
Output enable to output in low-Z	t _{OLZ}	5	—	5	—	ns	2, 3
Chip deselect to output in high-Z	t _{CHZ}	0	20	0	25	ns	1, 2, 3
LB#, UB# disable to high-Z	t _{BHZ}	0	20	0	25	ns	1, 2, 3
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1, 2, 3

Write Cycle

		R1LV0414D					
		-5	SI	-7LI			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t _{WC}	55	_	70	_	ns	
Address valid to end of write	t _{AW}	50	_	60	_	ns	
Chip selection to end of write	t _{CW}	50	_	60	_	ns	5
Write pulse width	t _{WP}	40	_	50	_	ns	4
LB#, UB# valid to end of write	t _{BW}	50	_	55	_	ns	
Address setup time	t _{AS}	0	_	0	_	ns	6
Write recovery time	t _{WR}	0	_	0	_	ns	7
Data to write time overlap	t _{DW}	25	_	30	_	ns	
Data hold from write time	t _{DH}	0	_	0	_	ns	
Output active from end of write	t _{OW}	5	_	5	_	ns	2
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1, 2, 3
Write to output in high-Z	t _{WHZ}	0	20	0	25	ns	1, 2

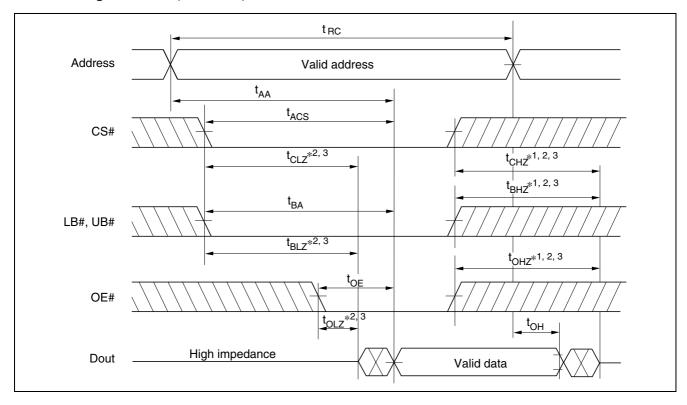
Notes: 1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

- 2. This parameter is sampled and not 100% tested.
- 3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
- 4. A write occurs during the overlap of a low CS#, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS# going low, WE# going low and LB# going low or UB# going low. A write ends at the earliest transition among CS# going high, WE# going high and LB# going high or UB# going high. twp is measured from the beginning of write to the end of write.
- 5. t_{CW} is measured from CS# going low to the end of write.
- 6. t_{AS} is measured from the address valid to the beginning of write.
- 7. t_{WR} is measured from the earlier of CS# or WE# going high to the end of write cycle.

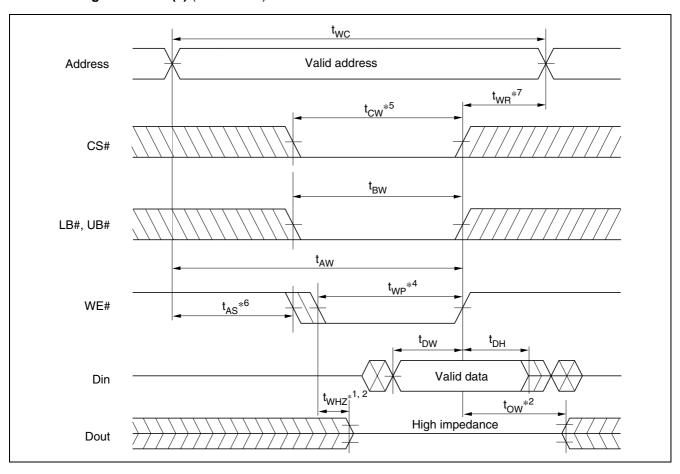
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Timing Waveform

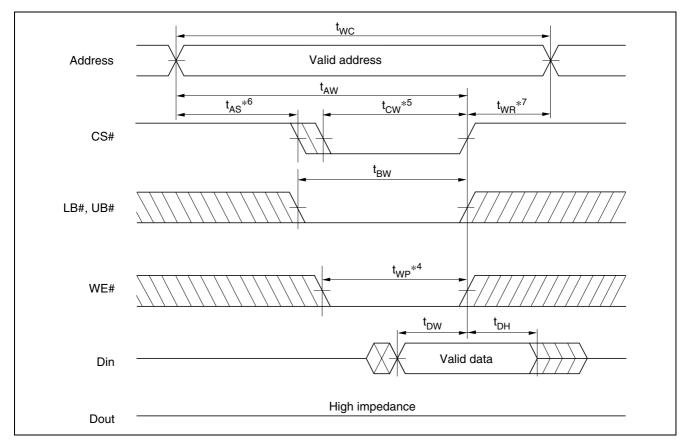
Read Timing Waveform (WE# = V_{IH})



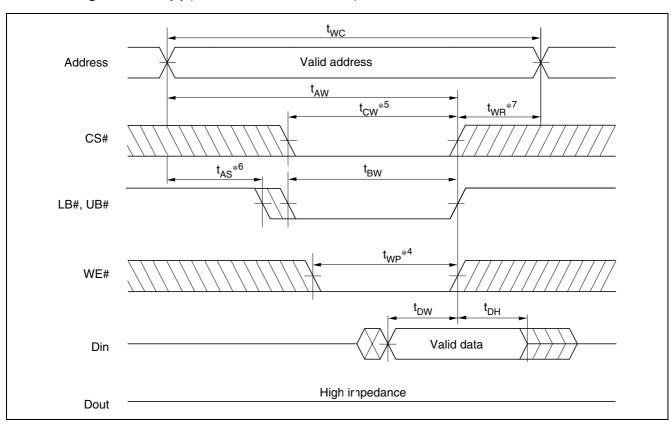
Write Timing Waveform (1) (WE# Clock)



Write Timing Waveform (2) (CS# Clock, OE# = V_{IH})



Write Timing Waveform (3) (LB#, UB# Clock, OE# = V_{IH})



Low V_{CC} Data Retention Characteristics

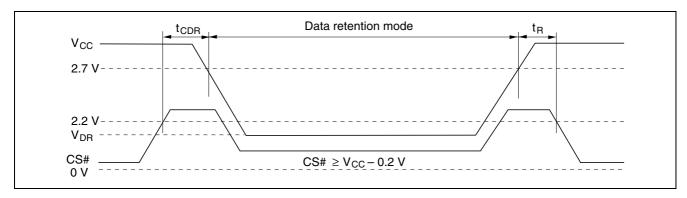
 $(Ta = -40 \text{ to } +85^{\circ}C)$

	Parameter			Min	Тур	Max	Unit	Test conditions
V _{CC} for data	a retention		V_{DR}	2		_	V	Vin ≥ 0V
								(1) CS# \geq V _{CC} $-$ 0.2 V or
								(2) LB# = UB# \geq V _{CC} $-$ 0.2 V,
								CS# ≤ 0.2 V
Data	-5SI	to +85°C	I _{CCDR}	—	1	10	μΑ	V _{CC} = 3.0 V, Vin ≥ 0V
retention		to +70°C	I _{CCDR}	_		8	μΑ	(1) $CS\# \ge V_{CC} - 0.2 \text{ V or}$
current		to +40°C	I _{CCDR}	_		3	μΑ	(2) LB# = UB# \geq V _{CC} $-$ 0.2 V,
		to +25°C	I _{CCDR}	_	1* ¹	2.5	μΑ	CS# ≤ 0.2 V
	-7LI	to +85°C	I _{CCDR}	_	_	20	μΑ	Average values
		to +70°C	I _{CCDR}	_	_	16	μΑ	
		to +40°C	I _{CCDR}	_	_	10	μΑ	
	to +25°C			_	1* ¹	10	μΑ	
Chip deselect to data retention time			t _{CDR}	0		_	ns	See retention waveform
Operation r	ecovery tim	ne	t _R	5		_	ms	

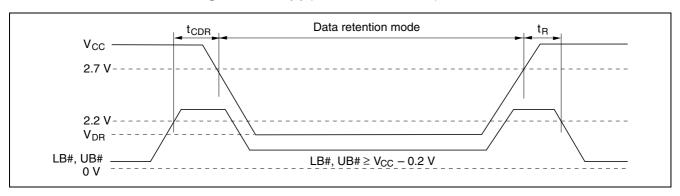
Note: 1. Typical values are at $V_{CC} = 3.0 \text{ V}$, $Ta = +25^{\circ}\text{C}$ and specified loading, and not guaranteed.

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Low V_{CC} Data Retention Timing Waveform (1) (CS# Controlled)



Low V_{CC} Data Retention Timing Waveform (2) (LB#, UB# Controlled)



Revision History

R1LV0414D Series Data Sheet

Rev.	Date		Contents of Modification
		Page	Description
0.01	Dec. 25, 2006	_	Initial issue
1.00	May. 24, 2007	2	Ordering Information
			R1LV0414DSB-5S% to R1LV0414DSB-5SI
			R1LV0414DSB-7L% to R1LV0414DSB-7LI
		2	Pin Arrangement
			A6 to A13, A13 to A6
		3	Change of Block Diagram
		4	Absolute Maximum Ratings: Deletion of R ver. specification
		4	DC Operating Conditions: Deletion of R ver. specification
		5	DC Characteristics
			I _{SB1} (-5SI) (to +25°C) max: 3 μA to 2.5 μA
		6	AC Characteristics: Change of Test Conditions
		11	Low V _{CC} Data Retention Characteristics
			I _{CCDR} (-5SI) (to +25°C) max: 3 μA to 2.5 μA
			Deletion of note 2

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